

The following document contains information on Cypress products. Although the document is marked with the name "Spansion" and "Fujitsu", the company that originally developed the specification, Cypress will continue to offer these products to new and existing customers.

Continuity of Specifications

There is no change to this document as a result of offering the device as a Cypress product. Any changes that have been made are the result of normal document improvements and are noted in the document history page, where supported. Future revisions will occur when appropriate, and changes will be noted in a document history page.

Continuity of Ordering Part Numbers

Cypress continues to support existing part numbers. To order these products, please use only the Ordering Part Numbers listed in this document.

For More Information

Please contact your local sales office for additional information about Cypress products and solutions.

About Cypress

Cypress (NASDAQ: CY) delivers high-performance, high-quality solutions at the heart of today's most advanced embedded systems, from automotive, industrial and networking platforms to highly interactive consumer and mobile devices. With a broad, differentiated product portfolio that includes NOR flash memories, F-RAM[™] and SRAM, Traveo[™] microcontrollers, the industry's only PSoC[®] programmable system-on-chip solutions, analog and PMIC Power Management ICs, CapSense[®] capacitive touch-sensing controllers, and Wireless BLE Bluetooth[®] Low-Energy and USB connectivity solutions, Cypress is committed to providing its customers worldwide with consistent innovation, best-in-class support and exceptional system value.

Ultra Low Voltage Boost Power management IC for Solar/Thermal **Energy Harvesting**

MB39C831

DESCRIPTION

The MB39C831 is the high-efficiency synchronous rectification boost DC/DC converter IC which efficiently supplies energy getting from the solar cell with the single cell or multiple cells, or from the thermoelectric generator (TEG) to the the Li-ion battery.

It contains the function to control the DC/DC converter output following the maximum power point of the solar cell (MPPT) and the protection function to charge the Li-ion battery safely.

It is possible to start-up from 0.35 V using the low-voltage process and adapts the applications which the single cell solar cell is treated as the input.

FEATURES

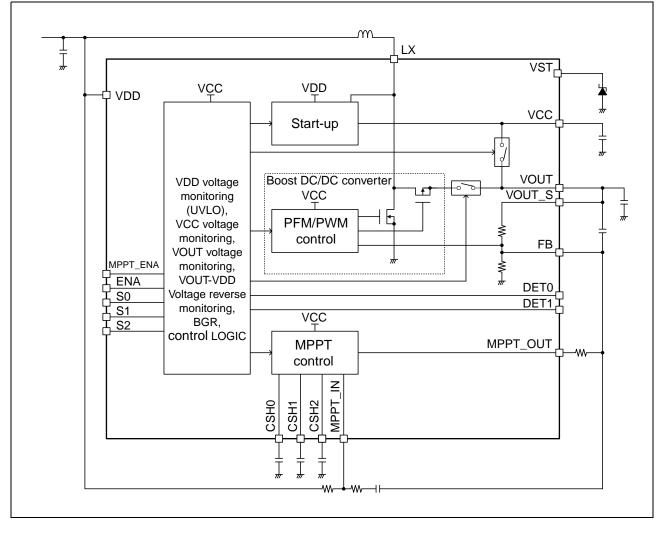
- · Operation input voltage range
- : 0.3 V to 4.75 V • Output voltage adjustment range : 3.0 V to 5.0 V
- Minimum input voltage at start-up : 0.35 V
- Quiescent Current (No load)
- : 41 µA : 200 mA
- Input peak current limit • Built-in MPPT
- Charge voltage to the Li-ion battery/current protection function built in
- Improvement of the efficiency during the low-output power according to the auto PFM/PWM switching mode

APPLICATIONS

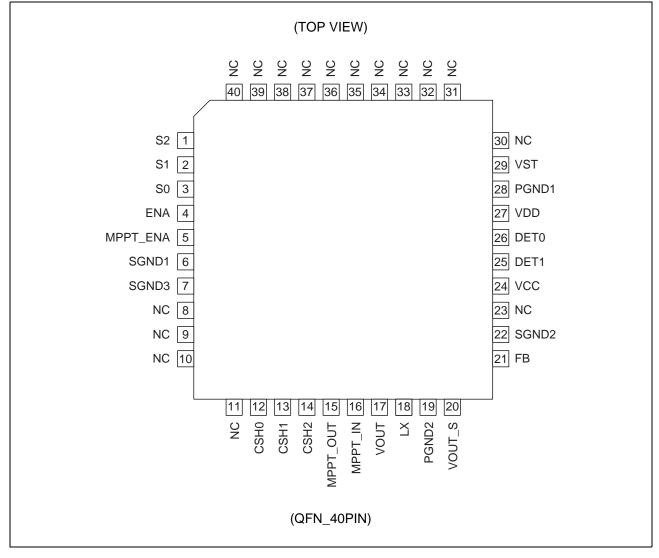
- Solar energy harvesting
- Thermal energy harvesting
- Li-ion battery using the single cell or multiple cells' solar cell/Super Capacitor Charger
- · Portable audio players
- Cellular phone
- eBook
- Electronic dictionary
- Wireless remote controllers
- Sensor node



BLOCK DIAGRAM



■ PIN ASSIGNMENTS



■ PIN DISCRIPTIONS

Pin No.	Pin Name	I/O	Description
1	S2	I	Input pin for preset output voltage setting and MPPT setting
2	S1	Ι	Input pin for preset output voltage setting and MPPT setting
3	S0	I	Input pin for preset output voltage setting and MPPT setting
4	ENA	Ι	DC/DC converter control input pin
5	MPPT_ENA	Ι	MPPT control input pin
6	SGND1		COMMON, MPPT block control system ground pin
7	SGND3		Control system ground pin for BGR
8 to 11	NC		Non connection pins
12	CSH0	0	Capacitor connection pin for MPPT, used only at the charge mode
13	CSH1	I	Capacitor connection pin for MPPT, used only at the charge mode
14	CSH2	Ι	Capacitor connection pin for MPPT, used only at the charge mode
15	MPPT_OUT	0	MPPT output pin, used only at the charge mode
16	MPPT_IN	I	MPPT input pin, used only at the charge mode
17	VOUT	0	Output pin of DC/DC converter
18	LX	I	Inductor connection pin
19	PGND2	—	DC/DC converter power system ground pin
20	VOUT_S	I	Input pin for DC/DC converter FB
21	FB	I	Feedback input pin of DC/DC converter
22	SGND2	—	DC/DC control system ground pin
23	NC		Non connection pin
24	VCC	0	Control system power supply output pin
25	DET1	0	Output pin for state notification
26	DET0	0	Output pin for state notification
27	VDD	I	External power supply input pin
28	PGND1		Start-up ground pin
29	VST	0	Start-up power supply output pin
30 to 40	NC		Non connection pins

Parameter	Symbol	Condition	Rat	Unit	
Farameter	Symbol	Condition	Min	Max	Unit
VDD input voltage	VVDDMAX	VDD pin	- 0.3	+ 7.0	V
VOUT input voltage	Vvoutmax	VOUT, VOUT_S pins	- 0.3	+ 7.0	V
Input pin input volt- age	Vvinputmax	MPPT_ENA, ENA, S0, S1, S2, CSH0, CSH1, CSH2, MPPT_IN, MPPT_OUT pins	- 0.3	VCC pin voltage $+ 0.3$ $(\le +7.0)$	V
Power dissipation	PD	Ta = + 85 °C	TBD	TBD	mW
Storage tempera- ture	Тѕтс	_	- 55	+ 125	°C
ESD voltage1	Vesdh	Human Body Model	- 2000	+ 2000	V
ESD voltage2	Vesdm	Machine Model	- 200	+ 200	V

WARNING: Semiconductor devices may be permanently damaged by application of stress (including, without limitation, voltage, current or temperature) in excess of absolute maximum ratings. Do not exceed any of these ratings.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Condition		Unit		
Falameter	Symbol	Condition	Min	Тур	Max	Unit
VDD input voltage	Vvdd	VDD pin	0.3	_	4.75	V
VOUT input voltage	Vvout	VOUT pin MPPT_ENA = H	2.55	3	5.5	V
Input pin input voltage	Vinput	MPPT_ENA, ENA, S0, S1, S2 pins	0		VCC pin voltage	V
Operating ambient temperature	Та		- 40		+ 85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated under these conditions.

Any use of semiconductor devices will be under their recommended operating condition. Operation under any conditions other than these conditions may adversely affect reliability of device and could result in device failure.

No warranty is made with respect to any use, operating conditions or combinations not represented on this data sheet. If you are considering application under any conditions other than listed herein, please contact sales representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

(Ta = − 40 °C to	+ 85 °C, irrespective of MPPT	ENA. $VDD \leq VOUT -$	0.25 V. L = 4.7 μH.	$Cout = 10 \mu F$)
(14 10 0.0			0. <u>_</u> 0 , <u>_</u> µ,	0 000 10 µl)

Doromotor	Cumb al	Condition		Value		
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Minimum input voltage at start-up	Vstart	VDD pin, Ta = +25 °C	_	0.35	0.5	V
		MPPT_ENA = L, S2 = L, S1 = L, S0 = L	2.940	3.000	3.060	V
		MPPT_ENA = L, S2 = L, S1 = L, S0 = H	3.234	3.300	3.366	V
Preset output voltage	Vout	MPPT_ENA = L, S2 = L, S1 = H, S0 = L	3.528	3.600	3.672	V
Fleset output voltage	VOUT	MPPT_ENA = L, S2 = L, S1 = H, S0 = H	4.018	4.100	4.182	V
		MPPT_ENA = L, S2 = H, S1 = L, S0 = L	4.410	4.500	4.590	V
		MPPT_ENA = L, S2 = H, S1 = L, S0 = H	4.900	5.000	5.100	V
		MPPT_ENA = H, S2 = L, S1 = L, S0 = L	45	50	55	%
		MPPT_ENA = H, S2 = L, S1 = L, S0 = H	50	55	60	%
		MPPT_ENA = H, S2 = L, S1 = H, S0 = L	55	60	65	%
MPPT setting	MPPTSET	MPPT_ENA = H, S2 = L, S1 = H, S0 = H	60	65	70	%
MFFT Setting	WIFFISEI	MPPT_ENA = H, S2 = H, S1 = L, S0 = L	65	70	75	%
		MPPT_ENA = H, S2 = H, S1 = L, S0 = H	70	75	80	%
		MPPT_ENA = H, S2 = H, S1 = H, S0 = L	75	80	85	%
		MPPT_ENA = H, S2 = H, S1 = H, S0 = H	80	85	90	%
LX peak current	LIMIN_A	LX pin input current	—	200		mA
Maximum output	Ιουτ	VDD = 0.6 V, VOUT = 3.3 V	8			mA
current	1001	VDD = 3.0 V, VOUT = 3.3 V	80			mA
Oscillation frequency	Fosc	PWM mode	0.87	1	1.13	MHz
Line regulation	VLINE	$0.4 \text{ V} \le \text{VDD} \le \text{VOUT} - 0.25 \text{ V}, \text{ IOUT} = 0$	—		0.5	%
Load regulation	Vload	VDD = 0.6 V, VOUT = 3.3 V, IOUT = 0 mA to 8 mA	_	_	0.5	%
Input power supply current		VDD pin input current , VDD = 0.6 V , VOUT = 3.3 V , IOUT = 0	_	0.75	5	mA
Current dissigntion		VOUT pin input current , MPPT_ENA = H, VOUT = 3.3 V , IOUT = 0		41	82	μA
Current dissipation	Ιοουτ	VOUT pin input current , MPPT_ENA = L, VOUT = 3.3 V , IOUT = 0	_	32	64	μΑ
UVLO release voltage	Vuvloh	_	0.2*	0.3*	0.4*	V
UVLO detection voltage	Vuvlol	_	0.1	0.2	0.3	V
VCC low-voltage detection 1	Vvccdeth	MPPT_ENA = L	2.8	2.9	3	V
VCC low-voltage detection release 1	VVCCDETL	MPPT_ENA = L, release voltage after de- tection	2.5	2.6	2.7	V
VCC low-voltage detection 2	Vvccdeth2	MPPT_ENA = H	2.5	2.6	2.7	V
VCC low-voltage detection release 2	VVCCDETL2	MPPT_ENA = H, release voltage after de- tection	2.45	2.55	2.65	V
VOUT low-voltage detection 1	Vvoutdeth	MPPT_ENA = L	2.8	2.9	3	V

(Continued)

(Continued)

Parameter	Symbol	Condition	Value			Unit
Farameter	Symbol	Condition	Min	Тур	Max	Unit
VOUT low-voltage detection release 1	Vvoutdetl	MPPT_ENA = L, release voltage after detection	2.5	2.6	2.7	V
VOUT low-voltage detection 2	Vvoutdeth2	MPPT_ENA = H	2.5	2.6	2.7	V
VOUT low-voltage detection release 2	Vvoutdetl2	MPPT_ENA = H, release voltage after detection	2.45	2.55	2.65	V
VOUT high-voltage detection	Vvoutdeth3	MPPT_ENA = H	3.88	4	4.12	V
VOUT high-voltage detection release	Vvoutdetl3	MPPT_ENA = H, release voltage after detection	3.58	3.7	3.82	V

*: This parameter is not be specified. This should be used as a reference to support designing the circuits.



OPERATION

The charge mode (MPPT_ENA = H) and the constant voltage mode (MPPT_ENA = L) are selected by the MPPT_ENA pin.

Charge mode : Follows the MPPT setting set at the S0, S1 and S2 pins and charges whilst letting VOUT be variable.

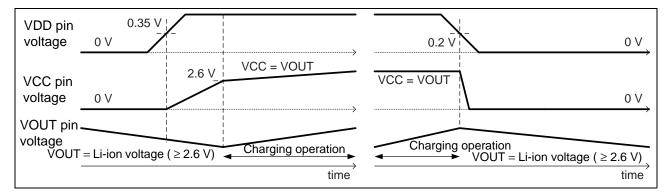
Constant voltage mode : Outputs VOUT set at the S0, S1 and S2 pins.

■ START-UP/SHUT-DOWN SEQUENCE

• When setting the charge mode

When 0.35 V or higher voltage which is the minimum input voltage at activation is applied to the VDD pin, the start-up circuit activates charging the VCC output. When VCC reaches 2.6 V, the DC/DC converter activates charging the VOUT output. At the same time, the start-up circuit stops operating. When VOUT reaches 2.9 V, the internal switch between VCC and VOUT is turned on and the charging starts connecting two outputs mutually.

When the VDD pin is equal to 0.2 V or less, the internal switch is turned off, and VOUT and VCC are disconnected.

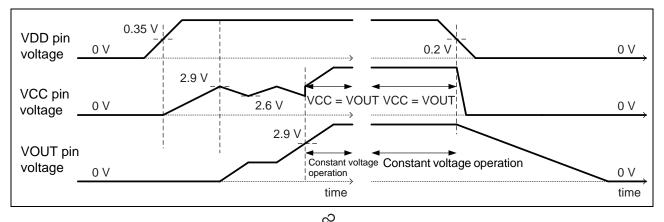


· When setting constant voltage mode

When 0.35 V or higher voltage which is the minimum input voltage at activation is applied to the VDD pin, the start-up circuit activates charging the VCC output. When VCC reaches 2.9 V, the DC/DC converter activates charging the VOUT output. At the same time, the start-up circuit stops the operation. When VCC becomes 2.6 V or less by the internal consumption current, the start-up circuit operates again, and this sequence is repeated till VOUT becomes the constant voltage. When VOUT reaches 2.9 V, the internal switch between VCC and VOUT is turned on and two outputs are connected mutually.

Afterwards, VOUT keeps rising, becomes the preset voltage set at the S0, S1 and S2 pins and outputs the constant voltage.

When the VDD pin becomes 0.2 V or less, the internal switch is turned off and VOUT and VCC are disconnected. As for VOUT, the output is gradually decreased by the leak current of the capacitor and so on.



■ MPPT

In general the solar cell, the voltage is fluctuated by the current which is the load. The voltage where the power becomes the maximum is called the power maximum voltage, and the voltage with no load is called the release voltage. The comparison between the power maximum voltage and release voltage is defined as the MPPT setting.

The DC/DC converter activates following the MPPT setting set at the S0, S1 and S2 pins for the charge mode.

When in use, please set this function after confirming the voltage dependency of the solar cell power.

■ FUNCTION

(1) Mode control

The mode is controlled by the MPPT_ENA pin. There are the charge mode and constant voltage mode, and the existence of the MPPT function, the UVLO function, the VDD, VCC, and VOUT voltage monitoring function is decided. Set the MPPT_ENA pin according to the application. The DC/DC operation is controlled by the ENA pin.

Input sigi	nal	Internal control	Function			
MPPT_ENA pin	ENA pin	State	МРРТ	UVLO, VCC low-voltage monitoring, VOUT low-voltage monitoring, state notification	VOUT high-voltage monitoring, VOUT-VDD voltage reverse monitoring	
L	L	Constant voltage mode, VOUT output stop	OFF	ON	OFF	
L	Н	Constant voltage mode, VOUT output enabled	OFF	ON	OFF	
н	L	Charge mode, Charge stop	OFF	ON	ON	
н	Н	Charge mode, Charge enabled	ON	ON	ON	

(2) Preset output voltage & MPPT setting

The state is controlled by the S0, S1 and S2 pins and the MPPT_ENA pin.

When MPPT_ENA pin is set to "L", S0, S1, S2 pins are used for the preset output voltage setting because the MPPT function is not used.

When MPPT_ENA pin is set to "H", S0, S1, S2 pins are used for MPPT setting.

	In	put signal	Contro	bl	
S2 pin	S1 pin	S0 pin	MPPT_ENA pin	Preset output voltage (V)	MPPT setting
L	L	L	L	3	Invalid
L	L	Н	L	3.3	Invalid
L	Н	L	L	3.6	Invalid
L	Н	Н	L	4.1	Invalid
Н	L	L	L	4.5	Invalid
Н	L	Н	L	5	Invalid
Н	Н	L	L	Setting prohibited	Setting prohibited
Н	Н	Н	L	Setting prohibited	Setting prohibited
L	L	L	н	Invalid	50%
L	L	Н	н	Invalid	55%
L	Н	L	н	Invalid	60%
L	Н	Н	н	Invalid	65%
Н	L	L	н	Invalid	70%
Н	L	Н	Н	Invalid	75%
Н	Н	L	Н	Invalid	80%
Н	Н	Н	Н	Invalid	85%

(3) UVLO

This function is independent of MPPT_ENA.

It monitors the drop of the VDD input voltage, and prevents IC's malfunction.

It has the hysteresis on the low-voltage side, and the detection state has been kept till the value becomes that voltage or less.

(4) VCC Under-voltage Monitoring

This function is independent of MPPT_ENA.

The detection that the VCC pin is equal to 2.9 V or higher is the source to start the operation of the DC/DC control part and to turn on the internal switch between VCC and VOUT. The undetected state is the VCC voltage undetected.

It has the hysteresis on the low-voltage side, and the detection state has been kept till the value becomes that voltage or less.

(5) VOUT Under-voltage Monitoring

This function controls the stop of charging when in the charge mode. The detection that the VOUT pin is equal to 2.6 V or less is the source to stop the DC/DC control part operation.

It has the hysteresis on the low-voltage side, and the detection state has been kept till the value becomes that voltage or less.

The function controls the internal switch between VCC and VOUT when in the constant mode.

The function detects that the VOUT pin is equal to 2.9 V or higher and then the internal switch between VCC and VOUT is turned on.

It has the hysteresis on the low-voltage side, and the detection state has been kept till the value becomes that voltage or less.

(6) VOUT Over-voltage Monitoring

This function operates in the charge mode (MPPT_ENA = H).

The detection that the VOUT pin is equal to 4.0 V or higher is the source to stop the DC/DC control part operation.

It has the hysteresis on the low-voltage side, and the detection state has been kept till the value becomes that voltage or less.

(7) VOUT-VDD Voltage Reverse Monitoring

This function operates in the charge mode (MPPT_ENA = H).

The detection that the VDD pin is equal to the VOUT pin's voltage or higher is the source to stop the DC/ DC control block operation.

(8) State Notification

This function is independent of MPPT_ENA.

It outputs the results of the VCC voltage monitoring, VOUT voltage monitoring and VOUT-VDD voltage reverse monitoring.

Output	singnal	State		
DET1 pin	DET0 pin	MPPT_ENA = L	MPPT_ENA = H	
L	L	Running (VCC < 2.9 V, VOUT < 2.9 V)	During VCC or VOUT low-voltage detection	
L	Н	Running (VCC \ge 2.9 V, VOUT < 2.9 V)	During VOUT-VDD voltage reverse detection*1	
Н	L	Normal (VCC \geq 2.9 V, VOUT \geq 2.9 V)	During VOUT high-voltage detection*2	
Н	Н	Running (VCC < 2.9 V, VOUT \ge 2.9 V)	Normal	

*1: The state during the VCC and VOUT low-voltage detection has the priority.

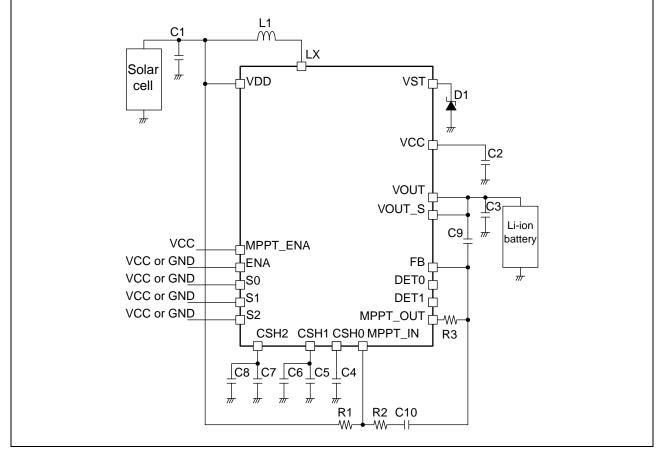
*2 : The states during the VCC and VOUT low-voltage detection and during the VOUT-VDD voltage reverse detection have the priority.

(9) Boost DC/DC converter

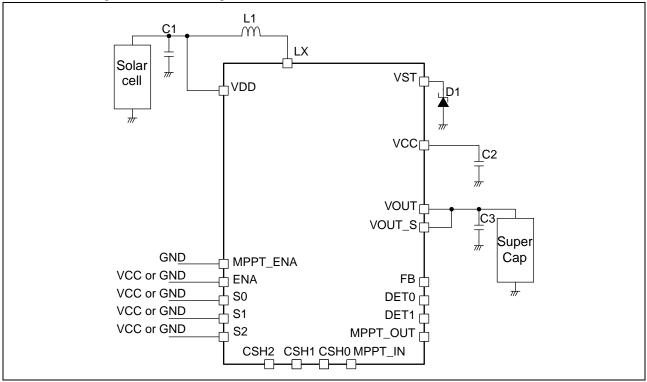
The function controls for the synchronous rectification operation of the main FET and synchronous FET using the frequency set by the built-in oscillator. The PFM operation is executed at the light load time. It has the output current limitation function to protect the circuit during the over load current. When the output current is excessive, the output voltage drops not to exceed the over current protection operation current, in order to prevent the IC destruction.

TYPICAL APPLICATIONS CIRCUIT

• When setting the charge mode



• When setting the constant voltage mode



• Parts list Part number Value Description C1 10 µF Capacitor C2 1 μF Capacitor C3 10 μF Capacitor C4 0.47 μF Capacitor C5 3300 pF Capacitor 4700 pF C6 Capacitor C7 0.1 μF Capacitor C8 47000 pF Capacitor C9 33 pF Capacitor C10 10 nF Capacitor R1 100 k Ω Resistor R2 $100 \ \text{k}\Omega$ Resistor R3 200 kΩ Resistor L1 4.7 μΗ Inductor D1 Zener diode ____



USAGE PRECAUTION

1. Do not configure the IC over the maximum ratings

If the IC is used over the maximum ratings, the LSI may be permanently damaged. It is preferable for the device to be normally operated within the recommended usage conditions. Usage outside of these conditions can have a bad effect on the reliability of the LSI.

2. Use the devices within recommended operating conditions

The recommended operating conditions are the recommended values that guarantee the normal operations of LSI.

The electrical ratings are guaranteed when the device is used within the recommended operating conditions and under the conditions stated for each item.

3. Printed circuit board ground lines should be set up with consideration for common impedance

4. Take appropriate measures against static electricity

- Containers for semiconductor materials should have anti-static protection or be made of conductive material.
- After mounting, printed circuit boards should be stored and shipped in conductive bags or containers.
- Work platforms, tools, and instruments should be properly grounded.
- Working personnel should be grounded with resistance of 250 k Ω to 1 $M\Omega$ in series between body and ground.

5. Do not apply negative voltages

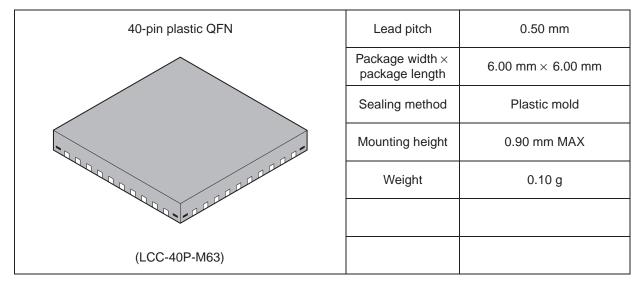
The use of negative voltages below -0.3 V may cause the parasitic transistor to be activated on LSI lines, which can cause malfunctions.

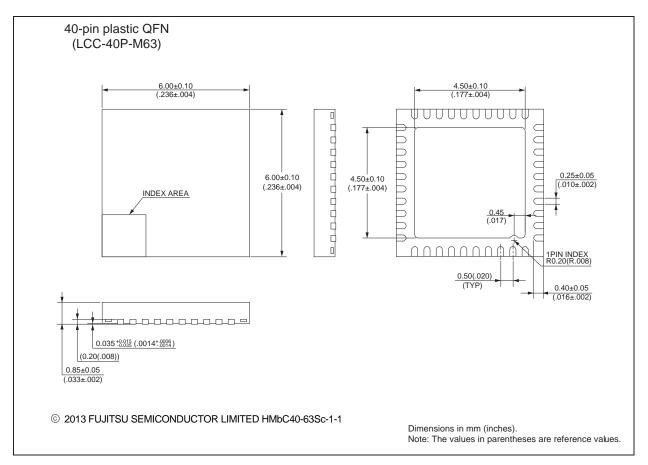
■ ORDERING INFORMATION

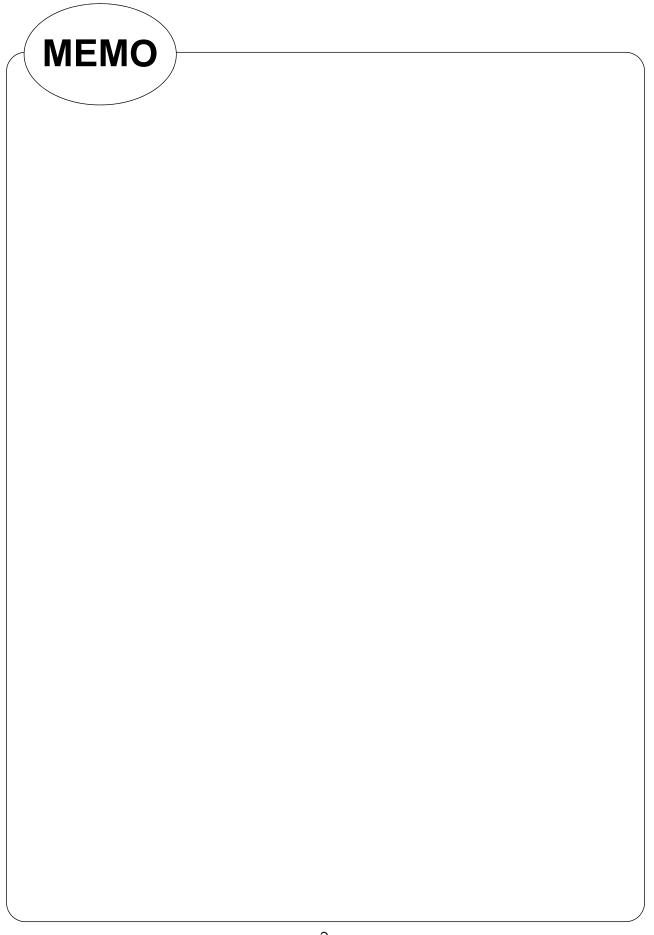
Part number	Package	Remarks
MB39C831QN	40-pin plastic QFN (LCC-40P-M63)	

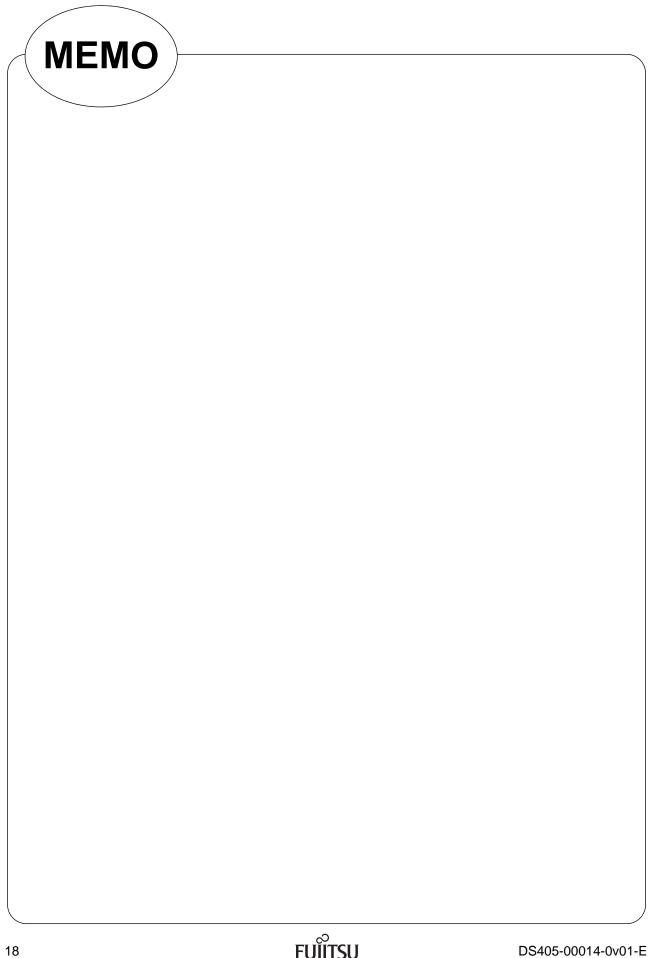


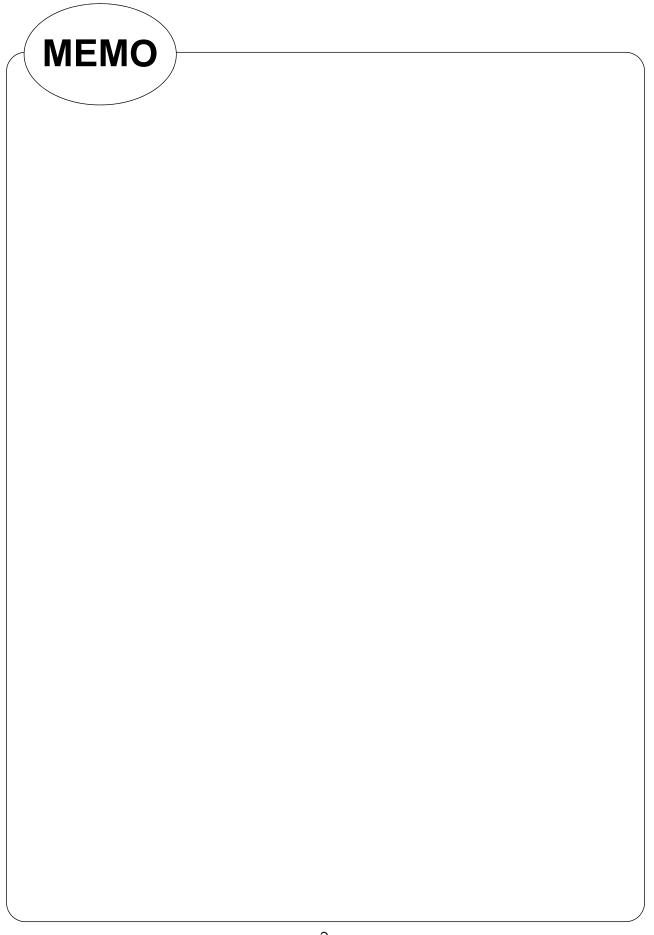
PACKAGE DIMENSIONS











FUJITSU SEMICONDUCTOR LIMITED

Nomura Fudosan Shin-yokohama Bldg. 10-23, Shin-yokohama 2-Chome, Kohoku-ku Yokohama Kanagawa 222-0033, Japan Tel: +81-45-415-5858 http://jp.fujitsu.com/fsl/en/

For further information please contact:

North and South America

FUJITSU SEMICONDUCTOR AMERICA, INC. 1250 E. Argues Avenue, M/S 333 Sunnyvale, CA 94085-5401, U.S.A. Tel: +1-408-737-5600 Fax: +1-408-737-5999 http://us.fujitsu.com/micro/

Europe

FUJITSU SEMICONDUCTOR EUROPE GmbH Pittlerstrasse 47, 63225 Langen, Germany Tel: +49-6103-690-0 Fax: +49-6103-690-122 http://emea.fujitsu.com/semiconductor/

Korea

FUJITSU SEMICONDUCTOR KOREA LTD. 902 Kosmo Tower Building, 1002 Daechi-Dong, Gangnam-Gu, Seoul 135-280, Republic of Korea Tel: +82-2-3484-7100 Fax: +82-2-3484-7111 http://www.fujitsu.com/kr/fsk/

Asia Pacific

FUJITSU SEMICONDUCTOR ASIA PTE. LTD. 151 Lorong Chuan, #05-08 New Tech Park 556741 Singapore Tel: +65-6281-0770 Fax: +65-6281-0220 http://sg.fujitsu.com/semiconductor/

FUJITSU SEMICONDUCTOR SHANGHAI CO., LTD. 30F, Kerry Parkside, 1155 Fang Dian Road, Pudong District, Shanghai 201204, China Tel: +86-21-6146-3688 Fax: +86-21-6146-3660 http://cn.fujitsu.com/fss/

FUJITSU SEMICONDUCTOR PACIFIC ASIA LTD. 2/F, Green 18 Building, Hong Kong Science Park, Shatin, N.T., Hong Kong Tel: +852-2736-3232 Fax: +852-2314-4207 http://cn.fujitsu.com/fsp/

All Rights Reserved.

FUJITSU SEMICONDUCTOR LIMITED, its subsidiaries and affiliates (collectively, "FUJITSU SEMICONDUCTOR") reserves the right to make changes to the information contained in this document without notice. Please contact your FUJITSU SEMICONDUCTOR sales representatives before order of FUJITSU SEMICONDUCTOR device. Information contained in this document, such as descriptions of function and application circuit examples is presented solely for reference to examples of operations and uses of FUJITSU SEMICONDUCTOR device. FUJITSU SEMICONDUCTOR disclaims any and all warranties of any kind, whether express or implied, related to such information, including, without limitation, quality, accuracy, performance, proper operation of the device or non-infringement. If you develop equipment or product incorporating the FUJITSU SEMICONDUCTOR device based on such information, you must assume any responsibility or liability arising out of or in connection with such information or any use thereof. FUJITSU SEMICONDUCTOR assumes no responsibility or liability for any damages whatsoever arising out of or in connection with such information or any use thereof.

Nothing contained in this document shall be construed as granting or conferring any right under any patents, copyrights, or any other intellectual property rights of FUJITSU SEMICONDUCTOR or any third party by license or otherwise, express or implied. FUJITSU SEMICONDUCTOR assumes no responsibility or liability for any infringement of any intellectual property rights or other rights of third parties resulting from or in connection with the information contained herein or use thereof.

The products described in this document are designed, developed and manufactured as contemplated for general use including without limitation, ordinary industrial use, general office use, personal use, and household use, but are not designed, developed and manufactured as contemplated (1) for use accompanying fatal risks or dangers that, unless extremely high levels of safety is secured, could lead directly to death, personal injury, severe physical damage or other loss (including, without limitation, use in nuclear facility, aircraft flight control system, air traffic control system, mass transport control system, medical life support system and military application), or (2) for use requiring extremely high level of reliability (including, without limitation, submersible repeater and artificial satellite). FUJITSU SEMICONDUCTOR shall not be liable for you and/or any third party for any claims or damages

and artificial satellite). POTTSO SEMICONDOCTOR shall not be hade for you and/or any tind party for any claims of dama arising out of or in connection with above-mentioned uses of the products. Any semiconductor devices fail or malfunction with some probability. You are responsible for providing adequate designs and safeguards against injury, damage or loss from such failures or malfunctions, by incorporating safety design measures into your facility, equipments and products such as redundancy, fire protection, and prevention of overcurrent levels and other abnormal operating conditions. The products and technical information described in this document are subject to the Foreign Exchange and Foreign Trade Control

Law of Japan, and may be subject to export or import laws or regulations in U.S. or other countries. You are responsible for ensuring compliance with such laws and regulations relating to export or re-export of the products and technical information described herein. All company names, brand names and trademarks herein are property of their respective owners.

Edited: Sales Promotion Department

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Power Management Specialised - PMIC category:

Click to view products by Cypress manufacturer:

Other Similar products are found below :

P9145-I0NQGI SLG7NT4192VTR AS3729B-BWLM LNBH25SPQR ADP5080ACBZ-1-RL MC32PF3000A6EP MB39C831QN-G-EFE2 MAX9959DCCQ+D MAX1932ETC+T MAX1856EUB+T STNRG011TR IRPS5401MXI03TRP S6AE102A0DGN1B200 MMPF0100FDAEP MCZ33903DS5EK S6AE101A0DGNAB200 MCZ33903DS3EK NCP6924CFCHT1G MAX17117ETJ+ L9916 L9915-CB MCZ33904D5EK MCZ33905DS3EK MMPF0100FCANES MCZ33905DD3EK MMPF0100FBANES WM8325GEFL/V MCZ33903DP5EK MCZ33905DS5EK MCZ33903D3EK MCZ33903DD5EK ADN8835ACPZ-R7 MCZ33903DP5EKR2 MCZ33903D5EK MCZ33903DD3EK MMPF0100FAAZES SLG7NT4198V MIC5164YMM P9180-00NHGI NCP6914AFCAT1G TLE9261QX TEA1998TS/1H MAX881REUB+T TLE9262QX TLE8880TN MAX8520ETP+T SLG7NT4083V ADP1031ACPZ-1-R7 ADP1031ACPZ-2-R7 ADP1031ACPZ-3-R7